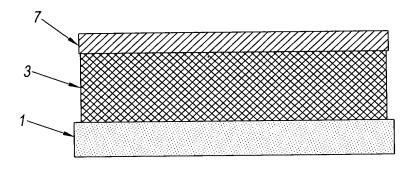
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Processing steps up to CMP

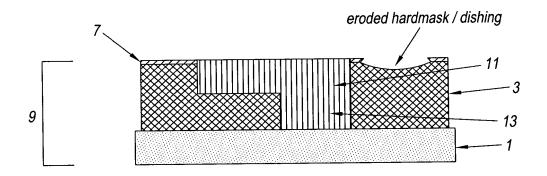
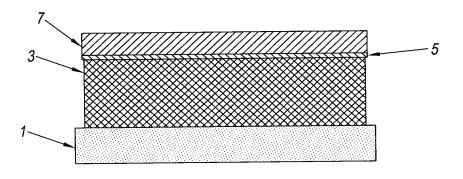
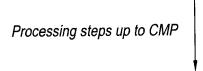


FIG. 1

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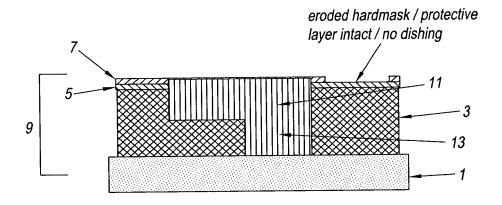
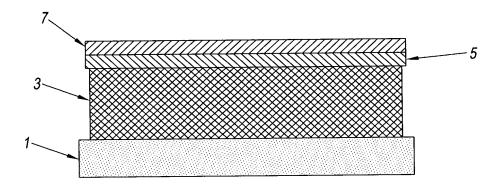


FIG. 2

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Processing steps up to CMP

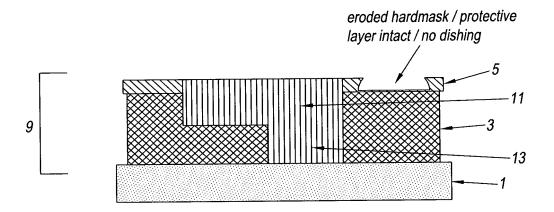


FIG. 3

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| 1) Spin Dielectric layer or layers |
|---|
| 2) Hot plate bake dielectric layer to crosslink (310°C, 2 min + 400°C, 2 min) |
| 3) Spin CMP protective layer |
| 4) Hot plate bake CMP protective layer (310°C, 2 min) |
| 5) Furnace Cure multilayer stack (415℃, 1hr) |
| Deposit Hardmask / CMP polish stop layer by conventional CVD methods |